

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRAL2023-18** is a Common Base Device Designed for Class C Amplifier Applications in L-Band FM Microwave Links.

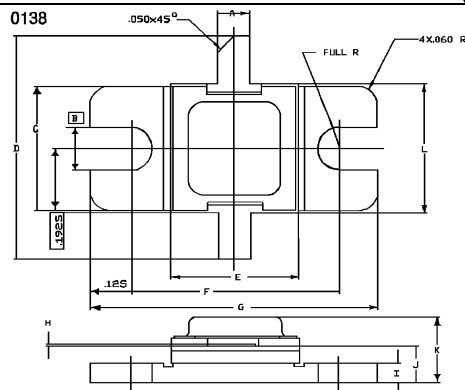
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Input/Output Matching

MAXIMUM RATINGS

I_C	4.0 A
V_{CES}	42 V
P_{DISS}	70 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$2.5^\circ C/W$

PACKAGE STYLE .250 2L FLG (C)



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.095/2.41	.105/2.67
B	.0125/3.18	
C	.380/9.65	.390/9.91
D	.780/19.81	
E	.392/9.96	.408/10.36
F	.645/16.38	.655/16.64
G	.895/22.73	.905/22.99
H	.002/0.05	.006/0.15
I	.055/1.40	.065/1.65
J	.105/2.67	.130/3.30
K		.230/5.84
L	.392/.408	.408/10.36

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 160$ mA	42			V
BV_{EBO}	$I_E = 2.0$ mA	3.5			V
I_{CBO}	$V_{CB} = 22$ V			4.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 800$ mA	10		100	---
P_G	$V_{CE} = 22$ V $f = 2000 - 2300$ MHz $P_{OUT} = 18.0$ W	7.0			dB
η_C		35			%